Microstructure characterization in dc sputtered a-SiC:H films by inert gas effusion measurements

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Abstract

The effusion of argon, neon and helium as well as of hydrogen was used for microstructure characterization of dc sputtered amorphous silicon carbon (a-SiC:H) alloys deposited with various carbon and hydrogen contents. Inert gas atoms were incorporated into the material by ion implantation. Our results suggest that effusion of implanted inert gas atoms is a useful method for microstructure characterisation of a-Si:C:H films.

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